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United States Patent [19]

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Zhao et al.

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[54] **METHOD OF MAKING A DUAL DAMASCENE INTERCONNECT STRUCTURE USING LOW DIELECTRIC CONSTANT MATERIAL FOR AN INTER-LEVEL DIELECTRIC LAYER**

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[52] U.S. Cl. **438/638**; 438/622; 438/623; 438/627; 438/643; 438/636; 438/637; 438/638; 438/648; 438/653; 438/656; 438/672; 438/685; 438/687; 438/902

[58] Field of Search 438/622, 623, 438/627, 637, 638, 639, 640, 666, 668.6, 672, 643, 678, 685, 902, 629, 636, 648, 653, 656, 687

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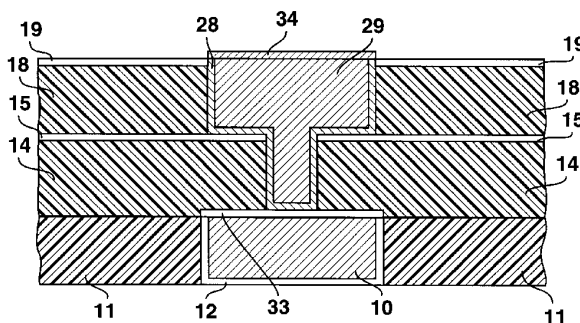
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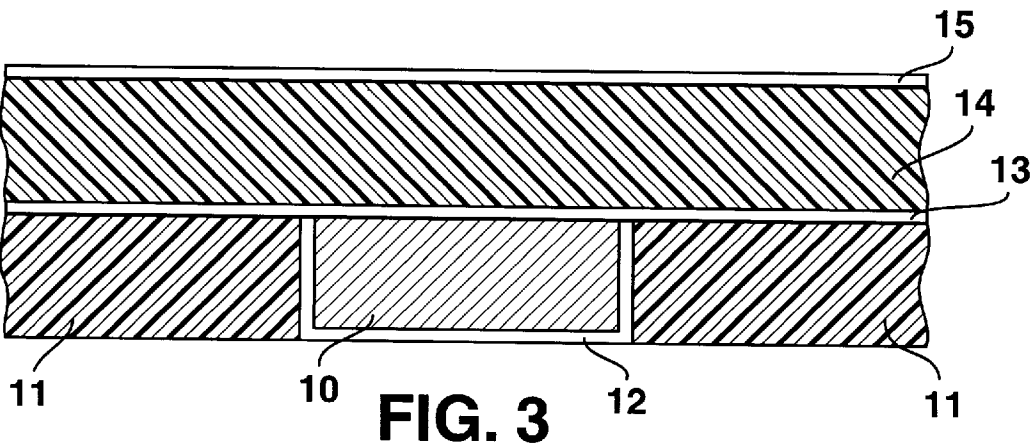
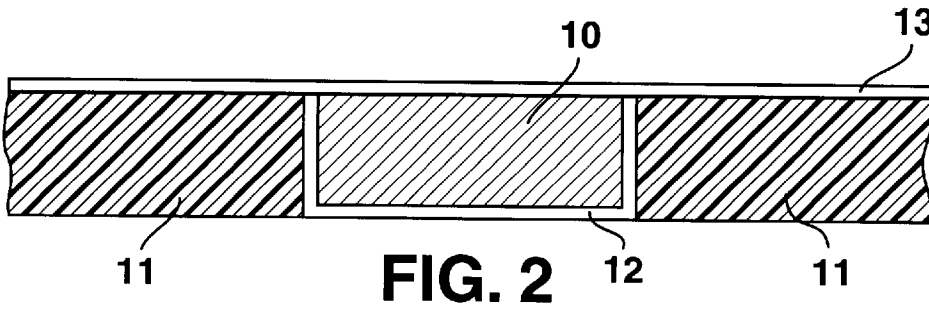
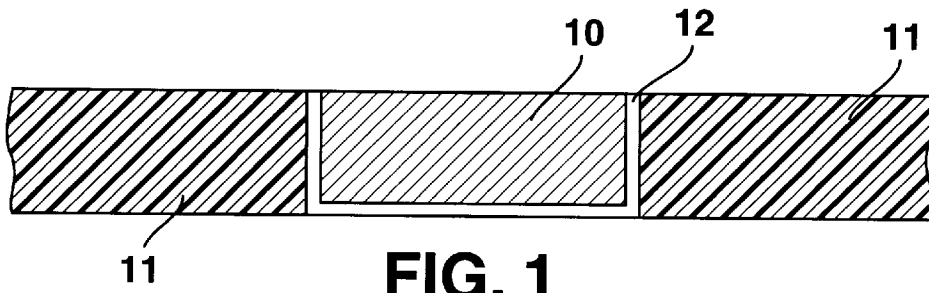
Primary Examiner—John F. Niebling
Assistant Examiner—David A. Zarneke

[57] ABSTRACT

A technique for fabricating a dual damascene interconnect structure using a low dielectric constant material as a dielectric layer or layers. A low dielectric constant (low-ε) dielectric material is used to form an inter-level dielectric (ILD) layer between metallization layers and in which via and trench openings are formed in the low-ε ILD. The dual damascene technique allows for both the via and trench openings to be filled at the same time.

12 Claims, 6 Drawing Sheets





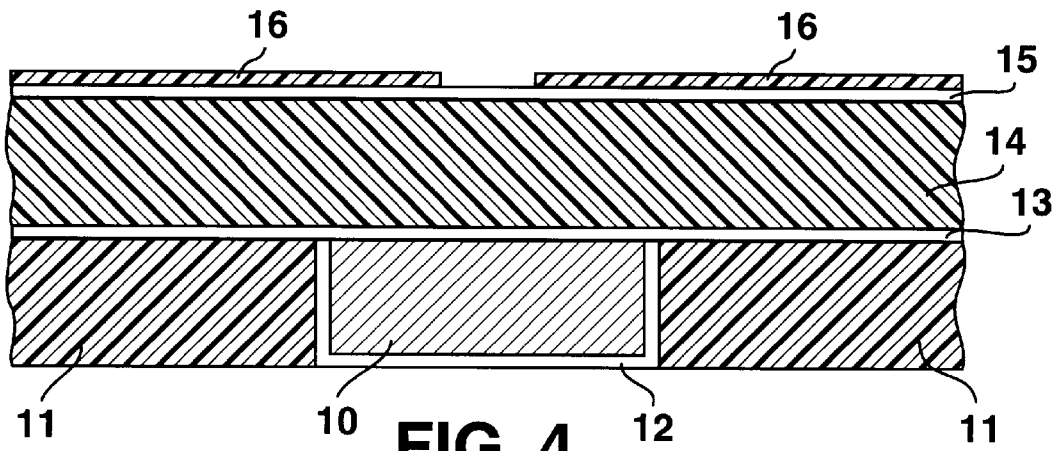


FIG. 4

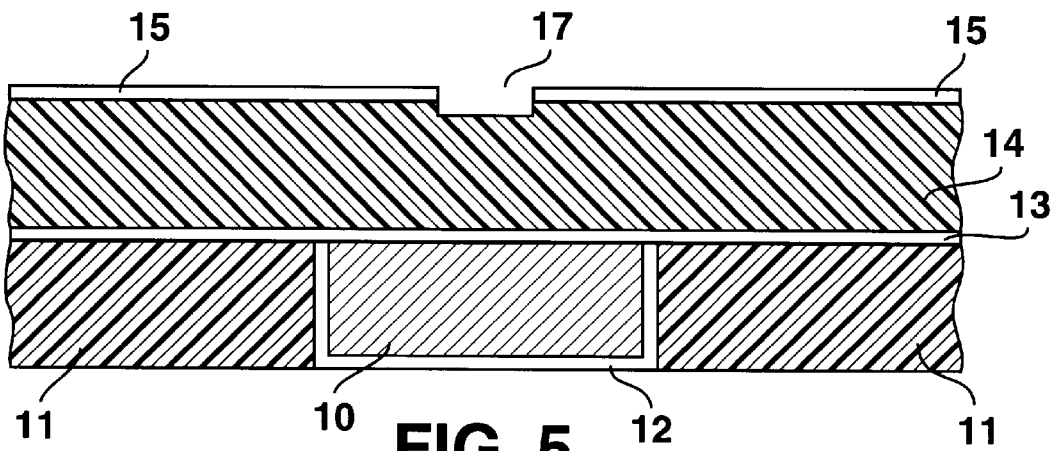


FIG. 5

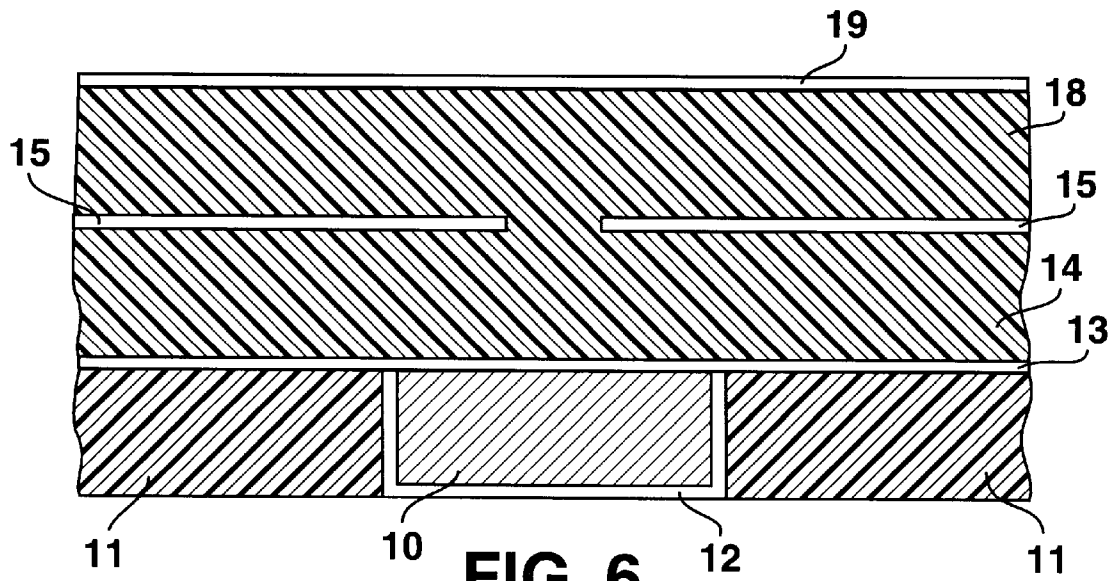
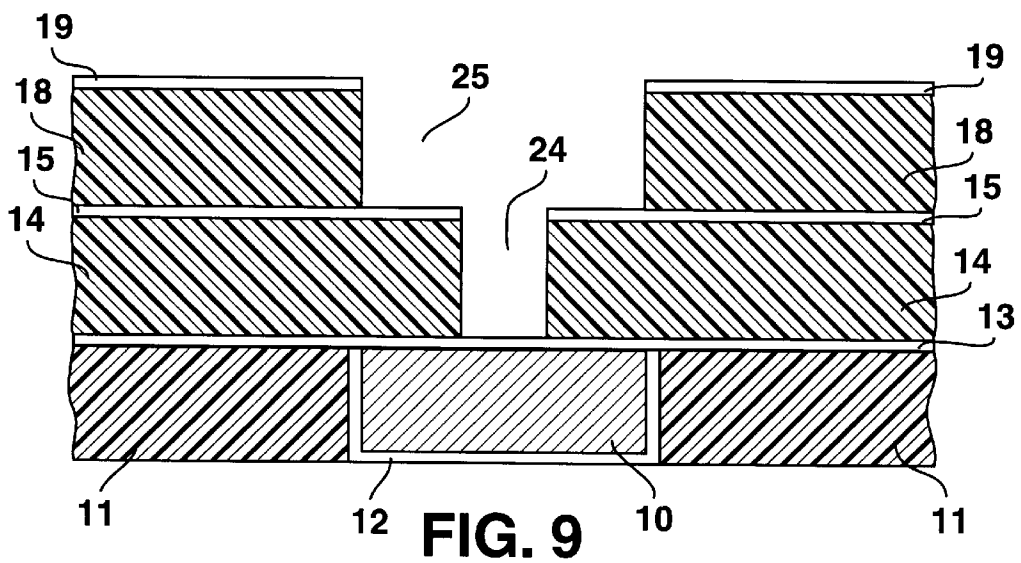
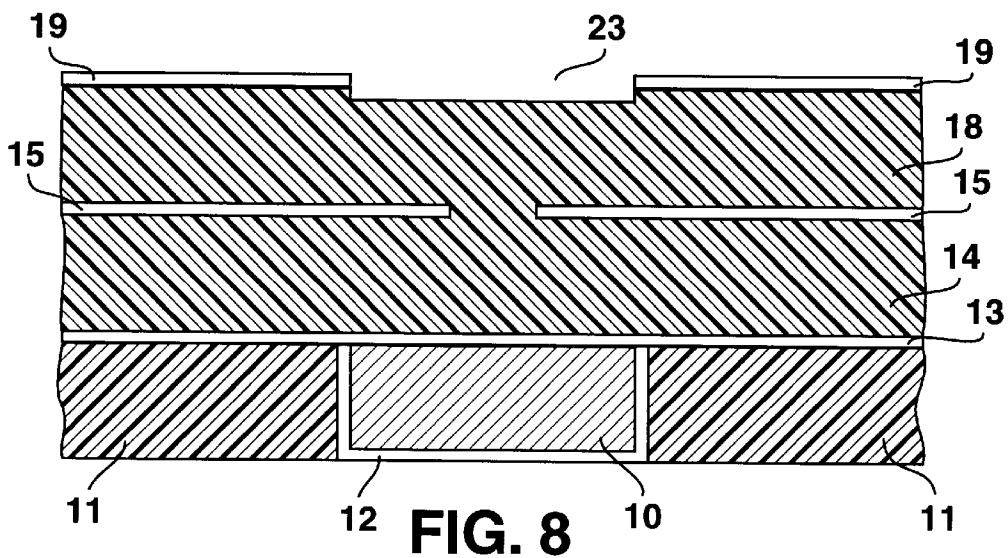
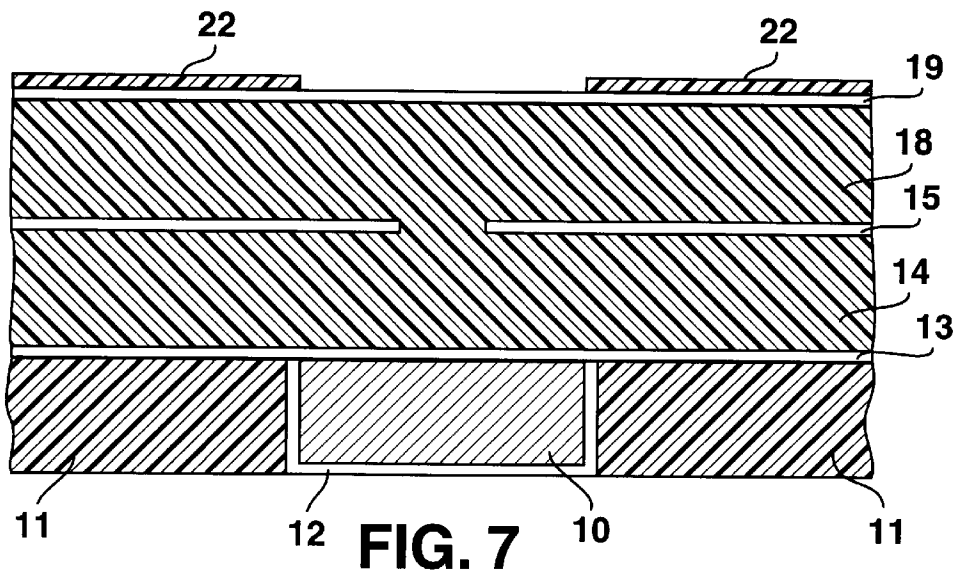
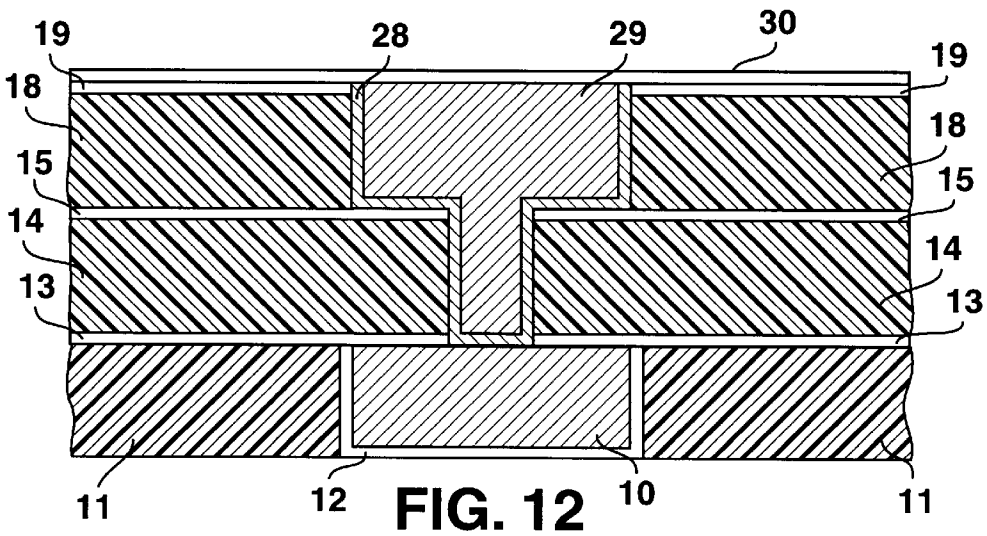
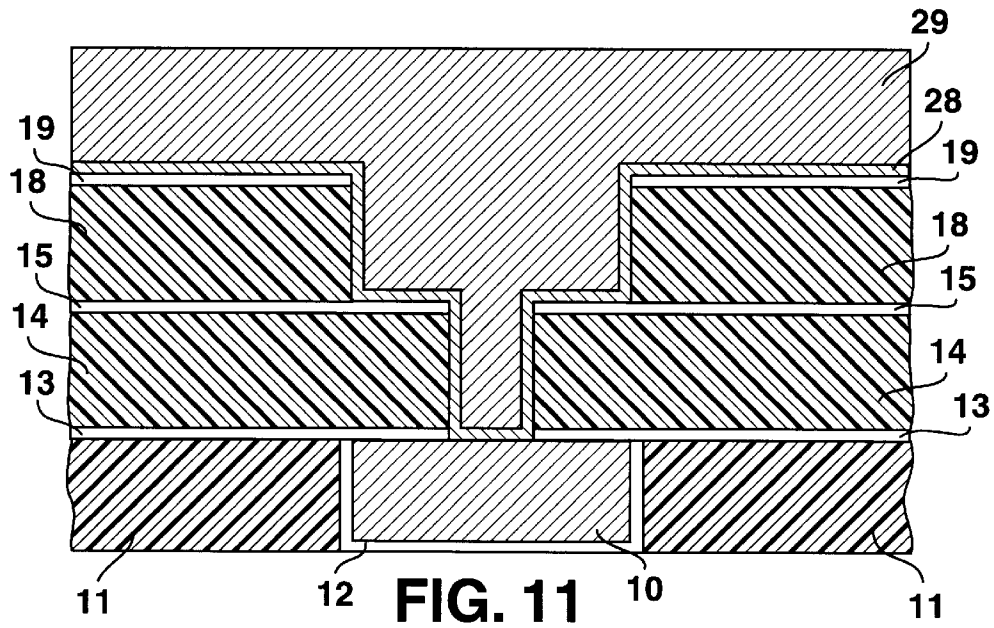
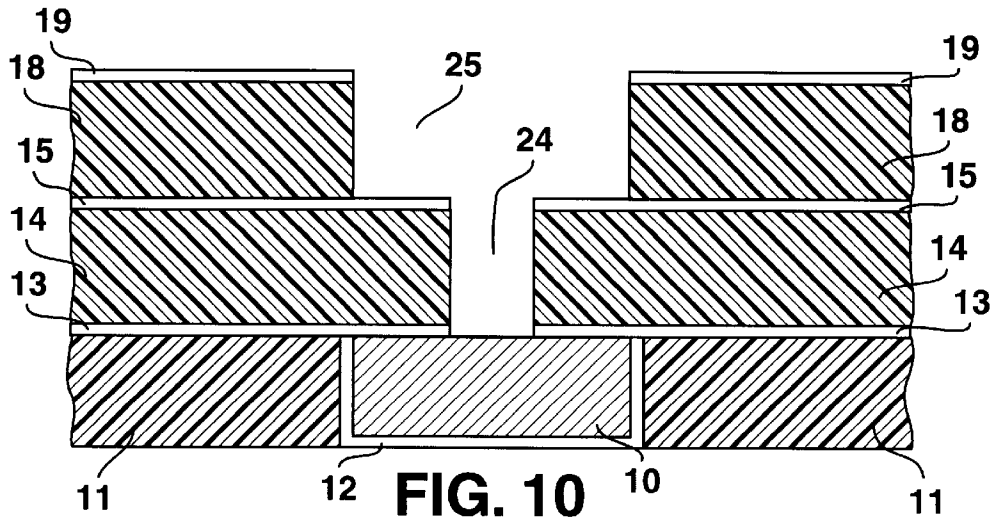


FIG. 6





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